

Complementary 20 V (D-S) Low-Threshold MOSFET

PRODUCT SUMMARY

	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
N-Channel	20	0.280 at V _{GS} = 4.5 V	1.28
		0.360 at V _{GS} = 2.5 V	1.13
		0.450 at V _{GS} = 1.8 V	1.00
P-Channel	- 20	0.490 at V _{GS} = - 4.5 V	- 1.00
		0.750 at V _{GS} = - 2.5 V	- 0.81
		1.10 at V _{GS} = - 1.8 V	- 0.67

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs: 1.8 V Rated
- Thermally Enhanced SC-70 Package
- Fast Switching
- Compliant to RoHS Directive 2002/95/EC

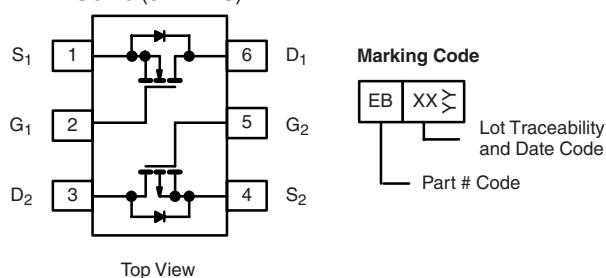


RoHS
COMPLIANT
HALOGEN
FREE
Available

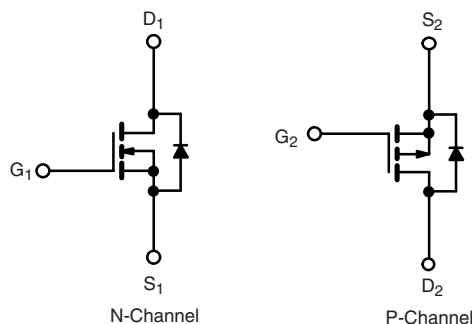
APPLICATIONS

- Load Switch for Portable Devices

SOT-363
SC-70 (6-LEADS)



Ordering Information: Si1563DH-T1-E3 (Lead (Pb)-free)
Si1563DH-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Symbol	N-Channel		P-Channel		Unit
		5 s	Steady State	5 s	Steady State	
Drain-Source Voltage	V _{DS}	20		- 20		V
Gate-Source Voltage	V _{GS}	± 8		± 8		
Continuous Drain Current (T _J = 150 °C) ^a	I _D	1.28	1.13	- 1.00	- 0.88	A
		0.92	0.81	- 0.72	- 0.63	
Pulsed Drain Current	I _{DM}	4.0		- 3.0		
Continuous Source Current (Diode Conduction) ^a	I _S	0.61	0.48	- 0.61	- 0.48	
Maximum Power Dissipation ^a	P _D	0.74	0.57	0.30	0.57	W
		0.38	0.30	0.16	0.3	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150				°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	R _{thJA}	130	170	°C/W
	Steady State		170	220	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	80	100	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 100 μA	N-Ch	0.45	1	V	
		V _{DS} = V _{GS} , I _D = - 100 μA	P-Ch	- 0.45	1		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V	N-Ch P-Ch		± 100 ± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V	N-Ch		1	μA	
		V _{DS} = - 16 V, V _{GS} = 0 V	P-Ch		- 1		
		V _{DS} = 16 V, V _{GS} = 0 V, T _J = 85 °C	N-Ch		5		
		V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 85 °C	P-Ch		- 5		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	N-Ch	2		A	
		V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	P-Ch	- 2			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 1.13 A	N-Ch		0.220	Ω	
		V _{GS} = - 4.5 V, I _D = - 0.88 A	P-Ch		0.400		
		V _{GS} = 2.5 V, I _D = 0.99 A	N-Ch		0.281		
		V _{GS} = - 2.5 V, I _D = - 0.71 A	P-Ch		0.610		
		V _{GS} = 1.8 V, I _D = 0.20 A	N-Ch		0.344		
		V _{GS} = - 1.8 V, I _D = - 0.20 A	P-Ch		0.850		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 1.13 A	N-Ch		2.6	S	
		V _{DS} = - 10 V, I _D = - 0.88 A	P-Ch		1.5		
Diode Forward Voltage ^a	V _{SD}	I _S = 0.48 A, V _{GS} = 0 V	N-Ch		0.8	V	
		I _S = - 0.48 A, V _{GS} = 0 V	P-Ch		- 0.8		
Dynamic ^b							
Total Gate Charge	Q _g	N-Channel V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 1.13 A P-Channel V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 0.88 A	N-Ch		1.25	2	nC
Gate-Source Charge	Q _{gs}		P-Ch		1.2	1.8	
Gate-Drain Charge	Q _{gd}		N-Ch		0.21		
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 10 V, R _L = 20 Ω I _D ≅ 0.5 A, V _{GEN} = 4.5 V, R _g = 6 Ω P-Channel V _{DD} = - 10 V, R _L = 20 Ω I _D ≅ - 0.5 A, V _{GEN} = - 4.5 V, R _g = 6 Ω	N-Ch		15	25	ns
			P-Ch		18	30	
Rise Time	t _r		N-Ch		22	35	
			P-Ch		25	40	
Turn-Off Delay Time	t _{d(off)}		N-Ch		25	40	
			P-Ch		15	25	
Fall Time	t _f		N-Ch		12	20	
			P-Ch		12	20	
Reverse Recovery Time	t _{rr}	I _F = 0.48 A, dI/dt = 100 A/μs	N-Ch		30	60	
			P-Ch		30	60	

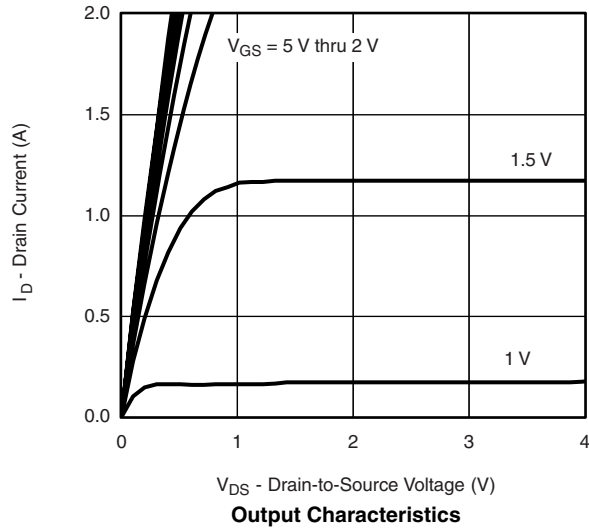
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

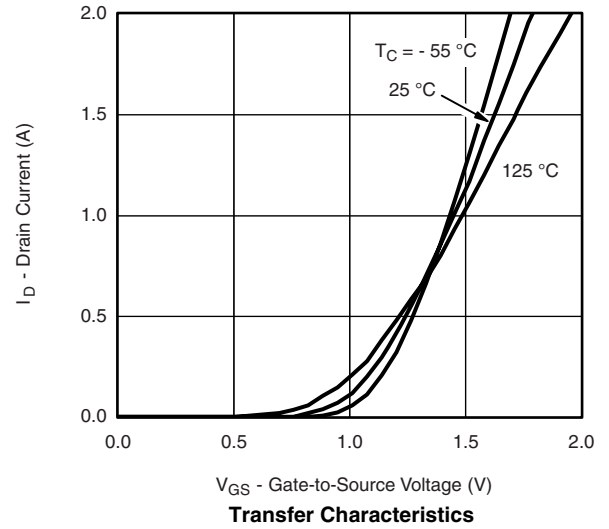
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

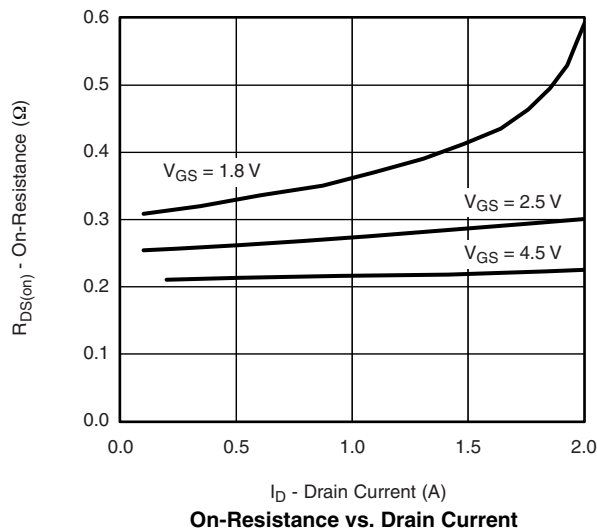
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



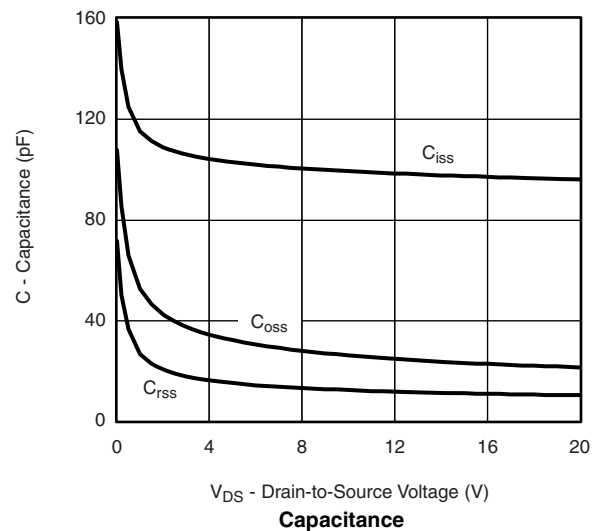
Output Characteristics



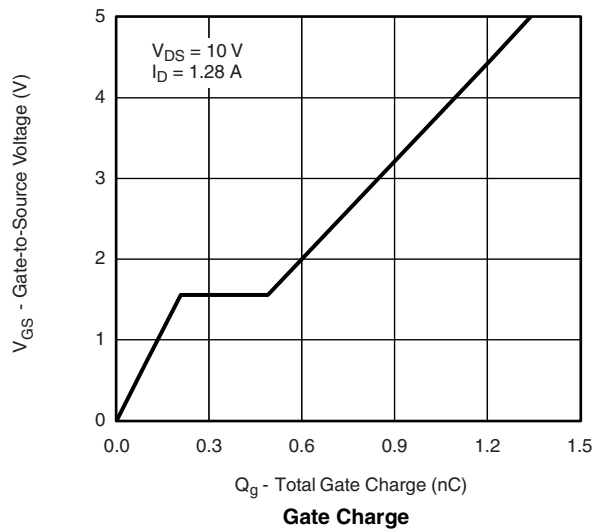
Transfer Characteristics



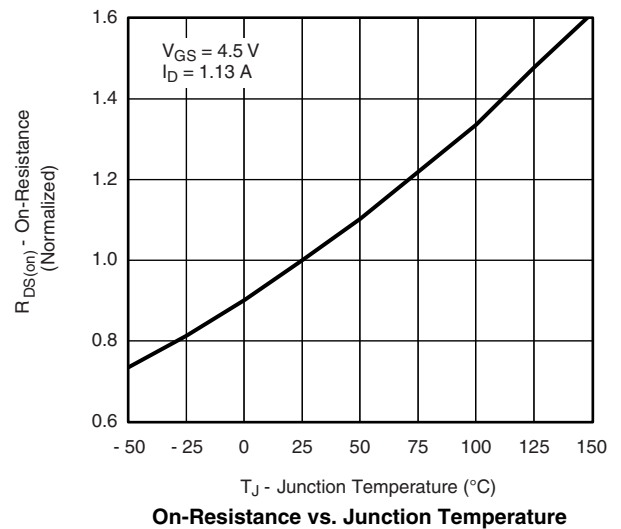
On-Resistance vs. Drain Current



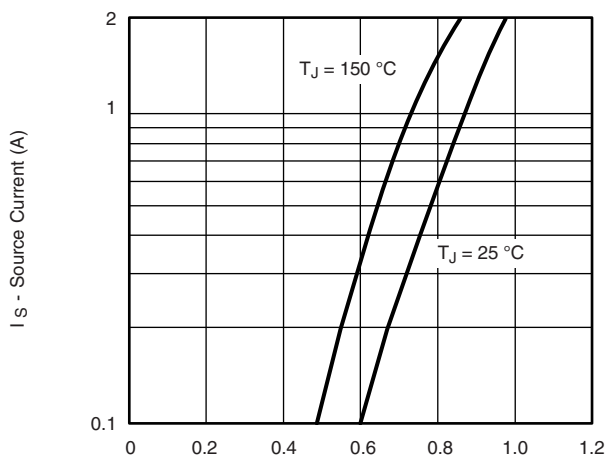
Capacitance



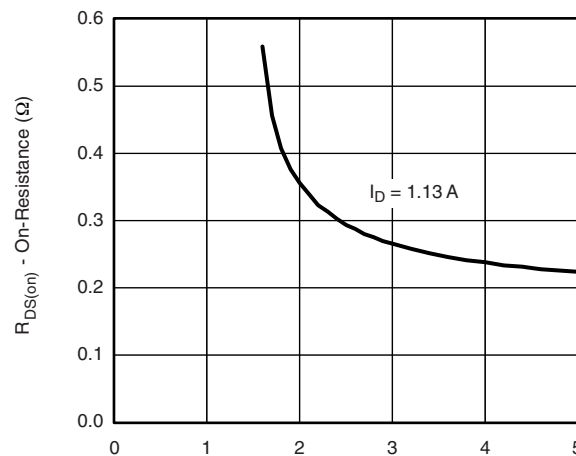
Gate Charge



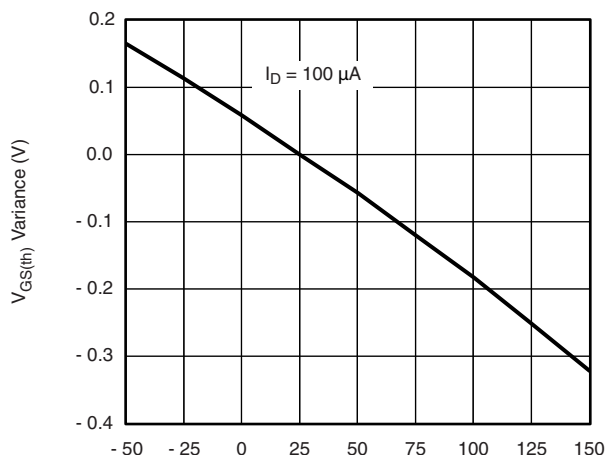
On-Resistance vs. Junction Temperature

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

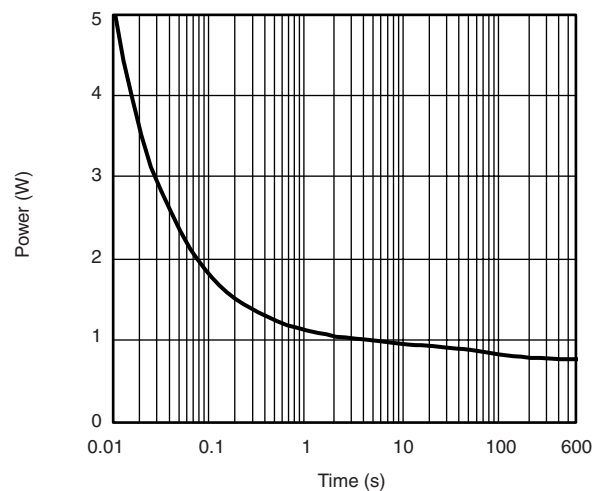
Source-Drain Diode Forward Voltage



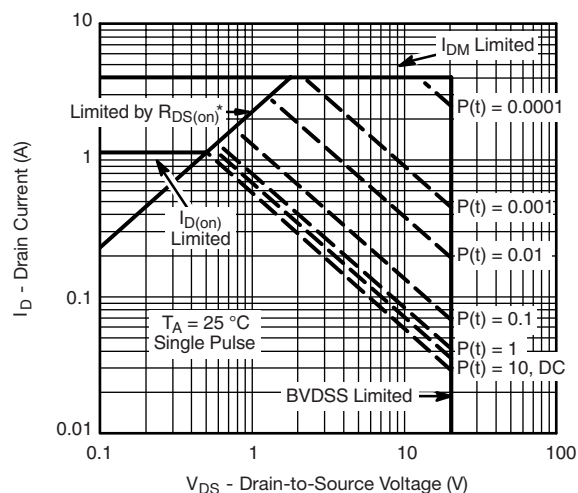
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

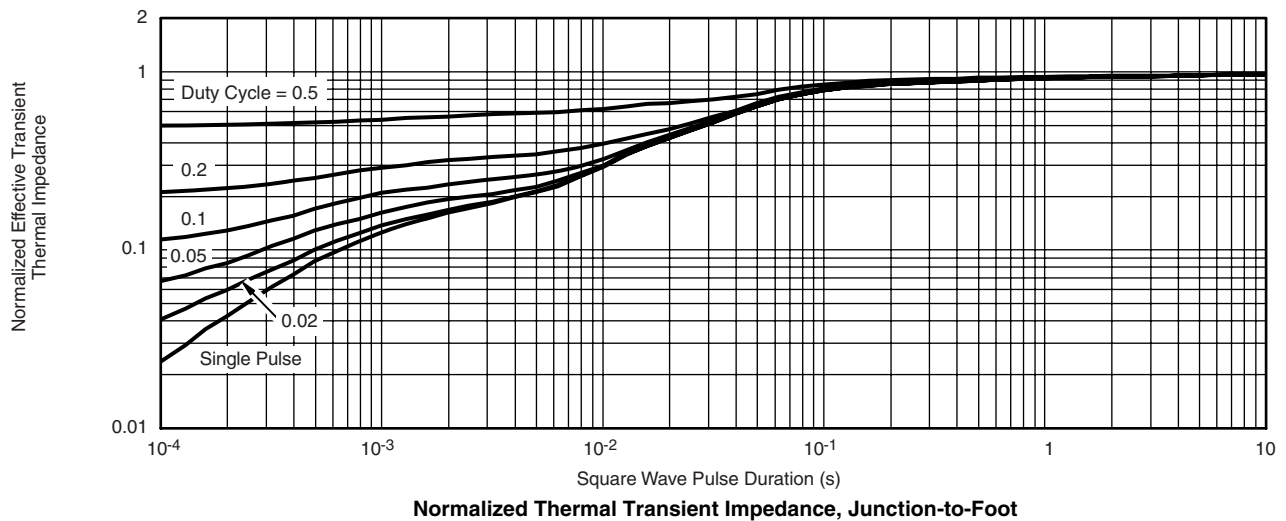
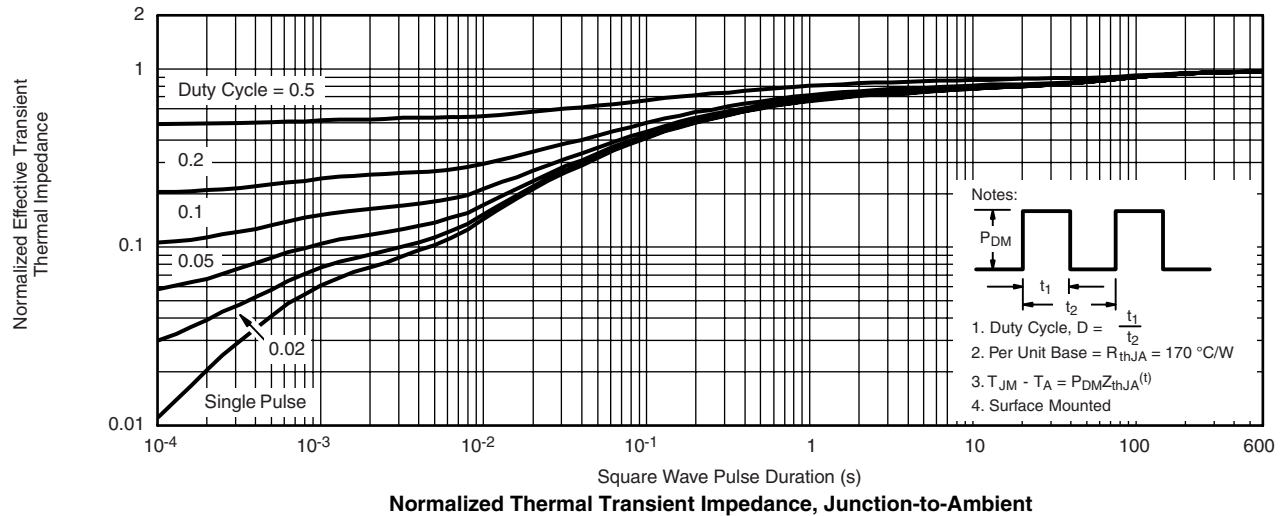


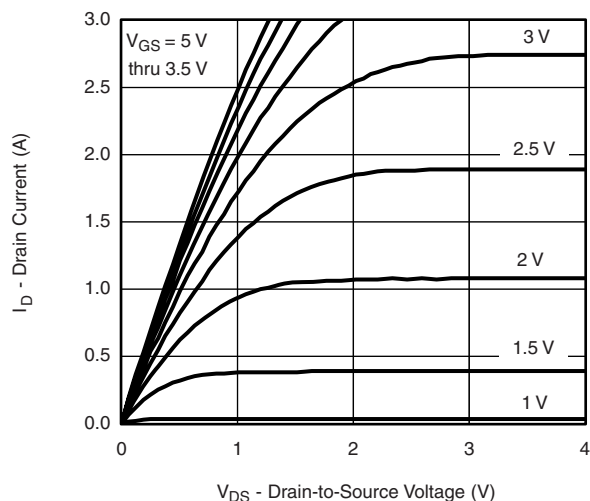
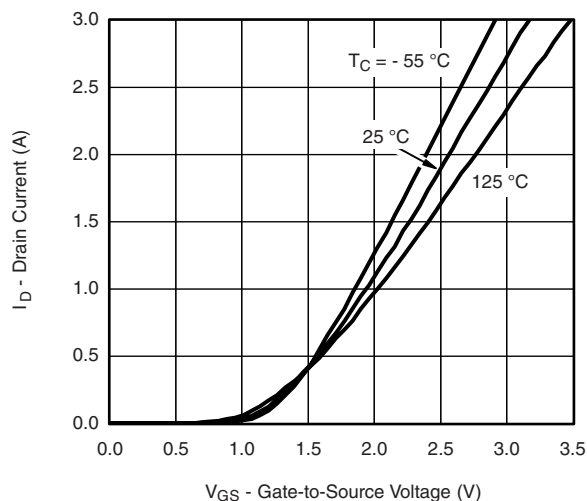
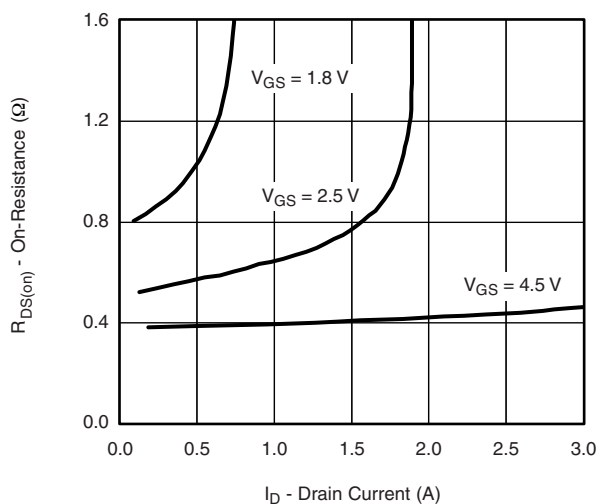
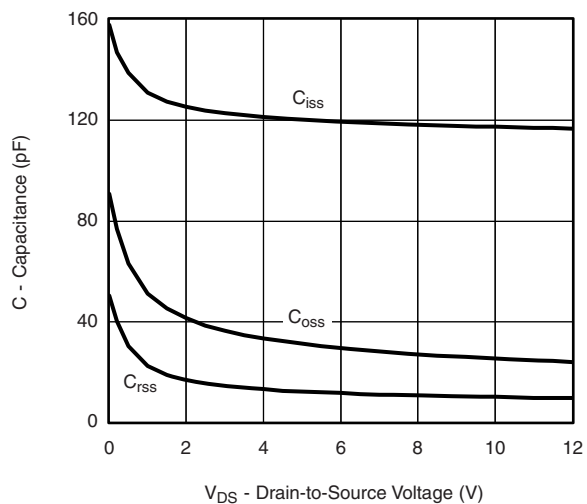
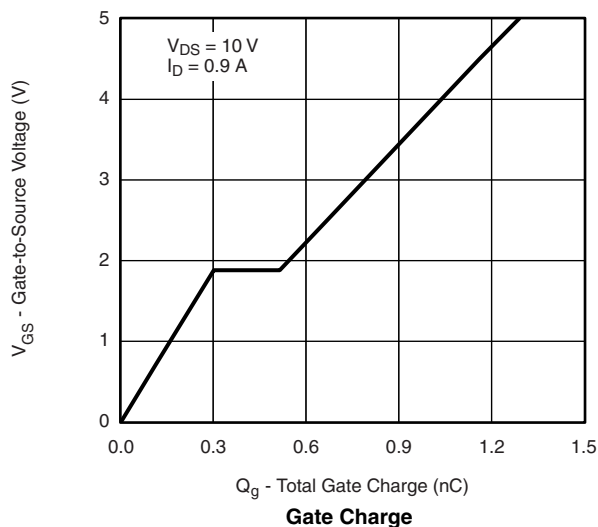
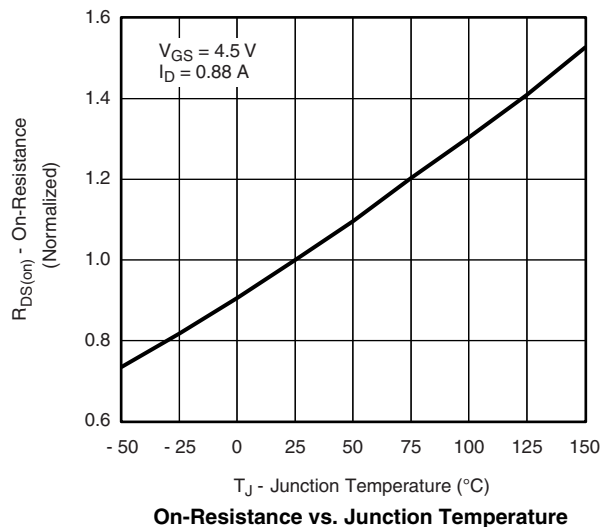
Single Pulse Power, Junction-to-Ambient



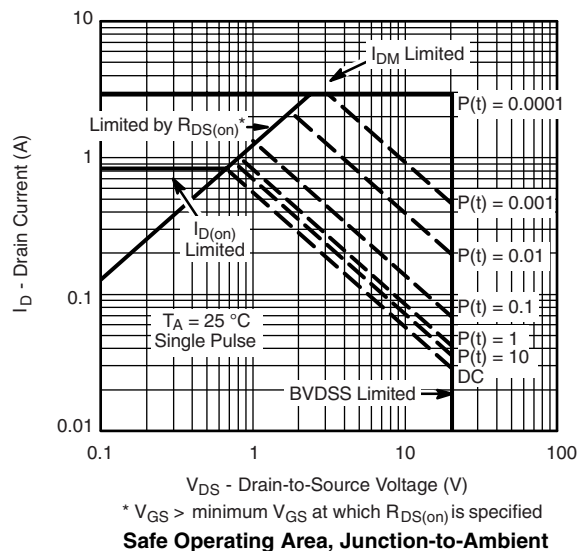
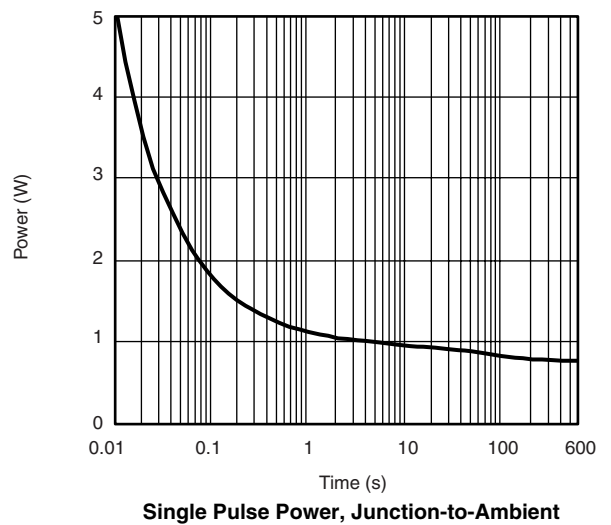
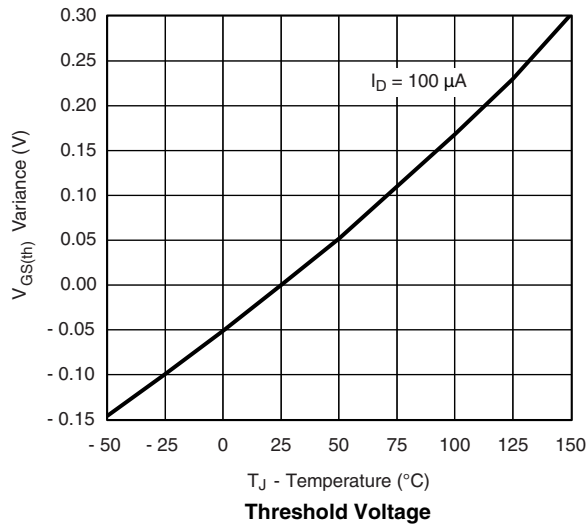
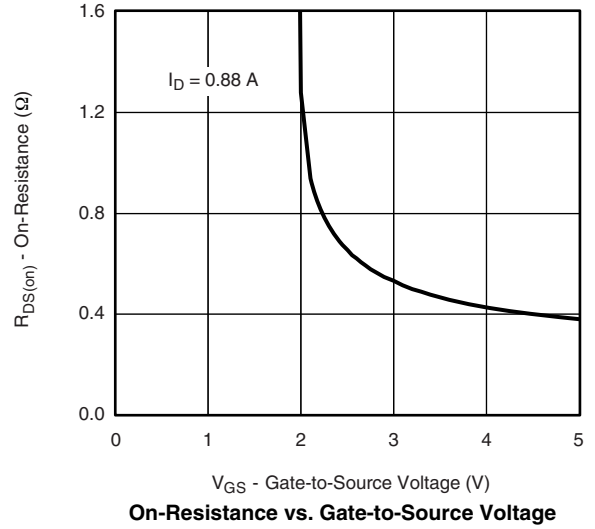
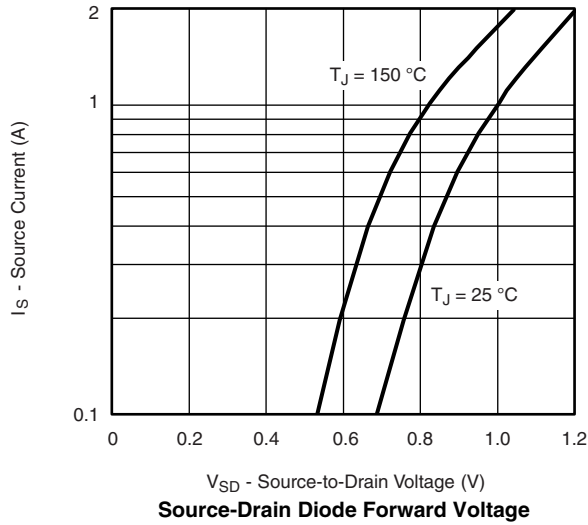
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient

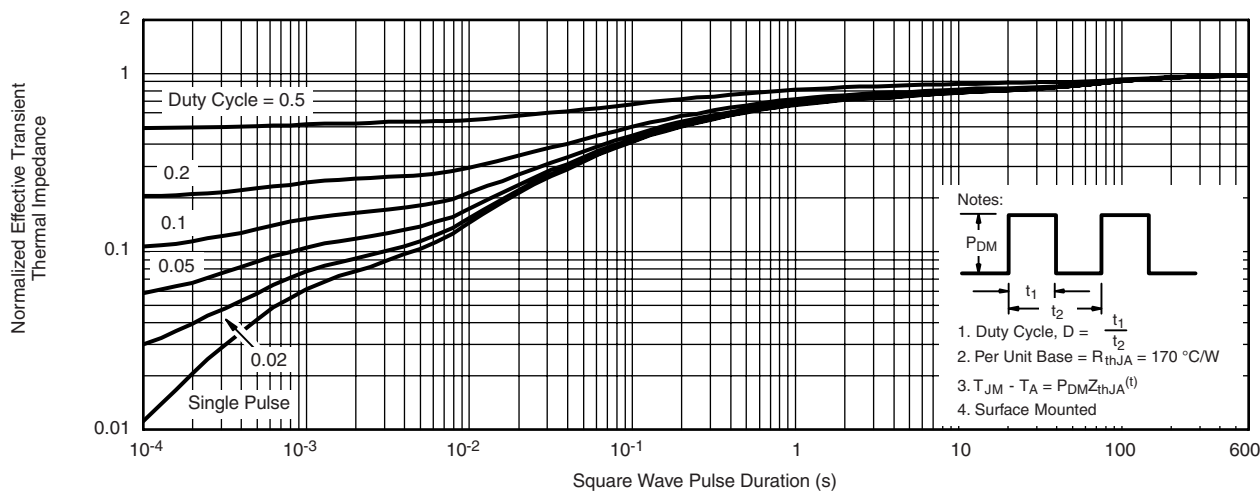
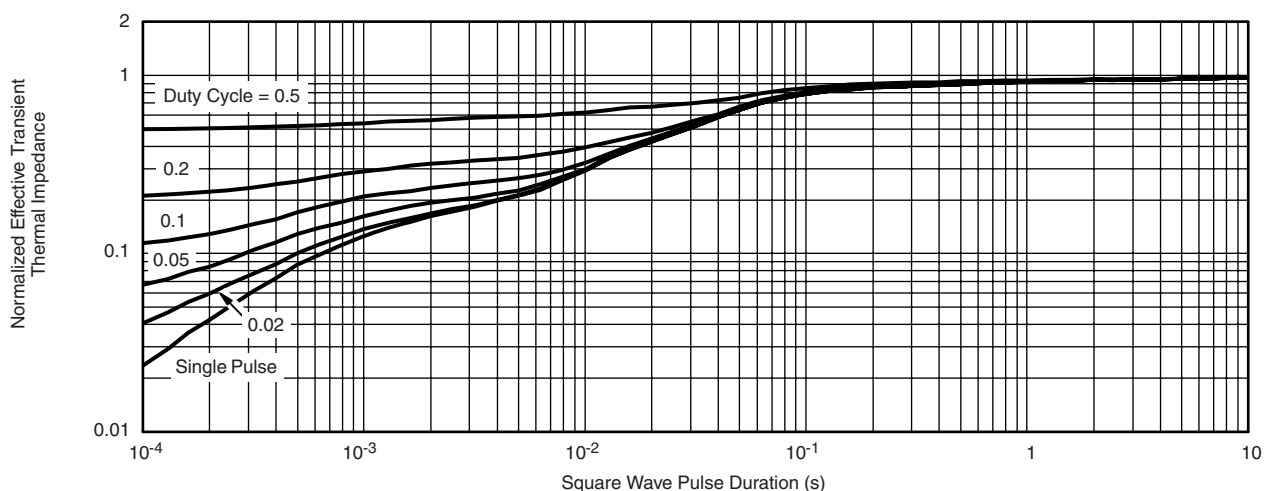
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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